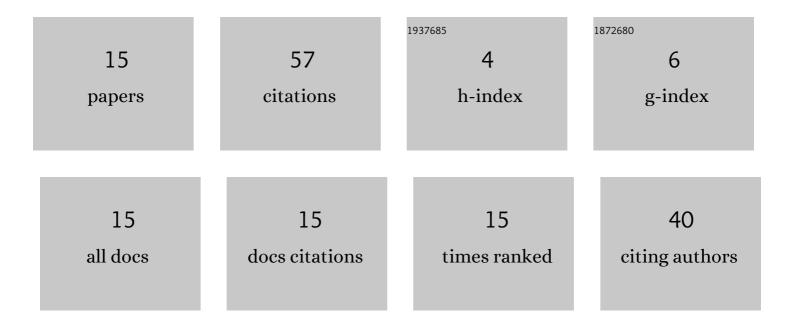
Pradipta Dutta

List of Publications by Year in descending order

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Ροληίοτλ Πιιττλ

| # | Article | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Muti-Carrier CDMA overview with BPSK modulation in Rayleigh channel. , 2010, , . | | 12 |
| 2 | Impact of high mobility Illâ€V compound material of a short channel thinâ€film SiGe double gate junctionless MOSFET as a source. Engineering Reports, 2020, 2, e12086. | 1.7 | 11 |
| 3 | A 2-D surface-potential-based threshold voltage model for short channel asymmetric heavily doped DG MOSFETs. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2014, 27, 682-690. | 1.9 | 6 |
| 4 | An Analytical BTBT Current Model of Symmetric/Asymmetric 4T Tunnel Double Gate FETs With Ambipolar Characteristic. IEEE Transactions on Electron Devices, 2016, 63, 2700-2707. | 3.0 | 6 |
| 5 | Comparison Study of DG-MOSFET with and without Gate Stack Configuration for Biosensor Applications. Silicon, 2022, 14, 3629-3640. | 3.3 | 6 |
| 6 | Improvement of transconductance and cut-off frequency in \$\$hbox {In}_{0.1}hbox {Ga}_{0.9}hbox {N}\$\$ back-barrier-based double-channel Al\$\$_{0.3}\$\$Ga\$\$_{0.7}\$\$NÂ/ÂGaN high electron mobility transistor by enhancing the drain source contact length ratio. Pramana - Journal of Physics, 2020, 94, 1. | 1.8 | 4 |
| 7 | Performance analysis of junctionless double gate MOSFET using Silicon and In <inf>0.53</inf> Ga <inf>0.47</inf> As. , 2016, , . | | 3 |
| 8 | Short-channel drain current model for asymmetric heavilyÂ/Âlightly doped DG MOSFETs. Pramana - Journal of Physics, 2017, 89, 1. | 1.8 | 3 |
| 9 | A dual gate material tunnel field effect transistor model incorporating twoâ€dimensional Poisson and Schrodinger wave equations. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 0, , e2933. | 1.9 | 2 |
| 10 | Improvement of transconductance and gate source capacitance of Al <inf>0.27</inf> Ga <inf>0.73</inf> N/GaN HEMT at 45nm gate length with In <inf>0.1</inf> Ga <inf>0.9</inf> N back-barrier. , 2017, , . | | 1 |
| 11 | Controlling of Floating-Body and Thermal Conductivity in Short Channel SOI MOSFET at 30Ânm Channel Node. Silicon, 0, , 1. | 3.3 | 1 |
| 12 | Improvements in FOMs and Thermal Effects of a III-V Compound Material Based Short-Channel Thin Film Junctionless Double Gate MOSFETs. ECS Journal of Solid State Science and Technology, 2021, 10, 111006. | 1.8 | 1 |
| 13 | Improvement in the Performance of III-V Channel Based Ultra-Thin Junction-Less-Hybrid CMOS Circuits with Mixed Mode Analysis. ECS Journal of Solid State Science and Technology, 2022, 11, 051001. | 1.8 | 1 |
| 14 | Performance enhancement in Al <inf>0.3</inf> Ga <inf>0.7</inf> N/GaN HEMT based inverter using MOSHEMT. , 2017, , . | | 0 |
| 15 | Impact of Left Side Back Gate Misalignment Effect in an Analytical Tunneling Current Modeling of an Ultrathin Asymmetric DG TFET. Silicon, 2021, 13, 929-938. | 3.3 | Ο |

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